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- Low r<sub>DS(on)</sub> . . . 1.3 Ω Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Four Distinct Function Modes
- Low Power Consumption

#### description

This power logic 8-bit addressable latch controls open-drain DMOS transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multifunctional device capable of storing single-line data in eight addressable latches with 3-to-8 decoding or demultiplexing mode active-low DMOS outputs.

Four distinct modes of operation are selectable by controlling the clear ( $\overline{CLR}$ ) and enable ( $\overline{G}$ ) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable  $\overline{G}$  should be held high (inactive) while the address lines are changing. In the 3-to-8 decoding

DW											
(TOP VIEW)											
PGND	1	υ	20	] PGND							
V <sub>CC</sub> [	2		19	] CLR							
S0 [	3		18	] D							
DRAIN0	4		17	DRAIN7							
DRAIN1	5		16	DRAIN6							
DRAIN2	6		15	DRAIN5							
DRAIN3	7		14	DRAIN4							
S1 [	8		13	] <u>G</u>							
LGND	9		12	] S2							
PGND	10		11	] PGND							

FUNCTION TABLE

INF	PUT	s	OUTPUT OF	EACH					
CLR	GD		RGD		CLR G D		ADDRESSED DRAIN	OTHER DRAIN	FUNCTION
H H	L L	H L	L H	Q <sub>io</sub> Q <sub>io</sub>	Addressable Latch				
н	Н	Х	Q <sub>io</sub>	Q <sub>io</sub>	Memory				
L	L L	H L	L H	H H	8-Line Demultiplexer				
L	Н	Х	н	Н	Clear				

#### LATCH SELECTION TABLE

-	AIN
SO ADDR	RESSED
L	0
н	1
L	2
н	3
L	4
н	5
L	6
н	7
	L H L H

or demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 9, logic ground (LGND), and pins 1, 10, 11, and 20, power ground (PGND) must be externally made in a manner that reduces crosstalk between the logic and load circuits.

The TPIC6259 is characterized for operation over the operating case temperature range of  $-40^{\circ}$ C to  $125^{\circ}$ C.



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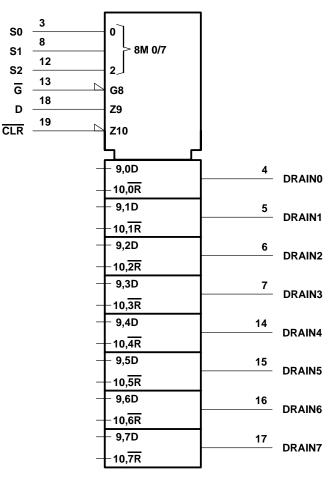
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#### logic symbol<sup>†</sup>

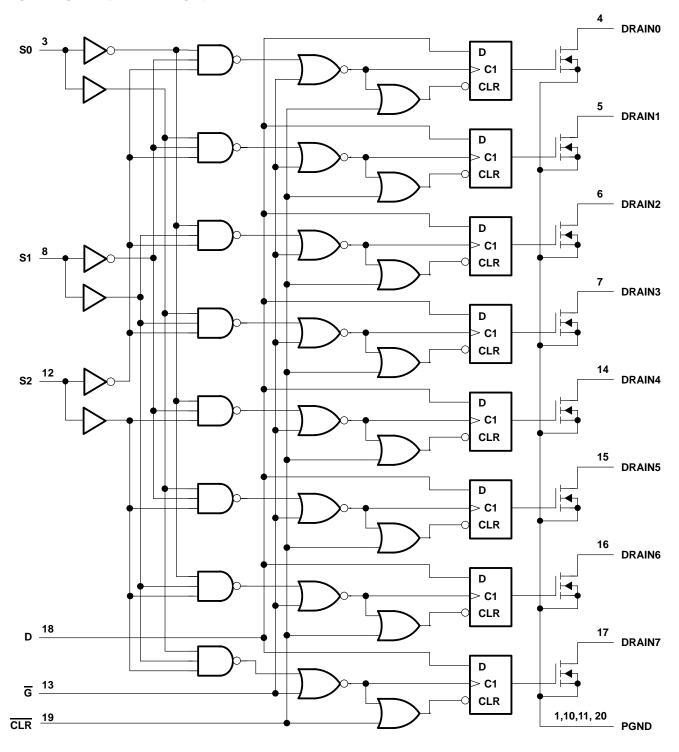


<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



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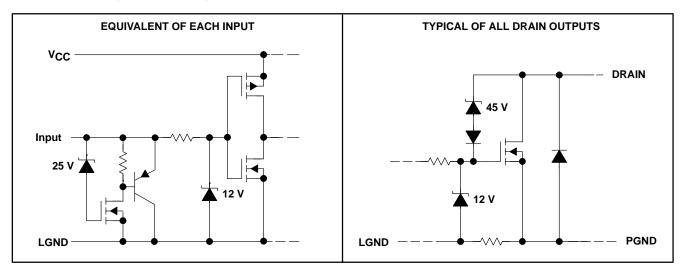
logic diagram (positive logic)





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#### schematic of inputs and outputs



# absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted) $\!\!\!\!^\dagger$

Logic supply voltage, V <sub>CC</sub> (see Note 1)	
Logic input voltage range, V <sub>I</sub>	–0.3 V to 7 V
Power DMOS drain-to-source voltage, V <sub>DS</sub> (see Note 2)	
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current	2 A
Pulsed drain current, each output, all outputs on, I <sub>Dn</sub> , T <sub>A</sub> = 25°C (see Note 3)	750 mA
Continuous drain current, each output, all outputs on, I <sub>Dn</sub> , T <sub>A</sub> = 25°C	250 mA
Peak drain current single output, I <sub>DM.</sub> T <sub>A</sub> = 25°C (see Note 3)	2 A
Single-pulse avalanche energy, E <sub>AS</sub> (see Note 4)	75 mJ
Avalanche current, I <sub>AS</sub> (see Note 4)	1 A
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T <sub>J</sub>	−40°C to 150°C
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to LGND and PGND.

- 2. Each power DMOS source is internally connected to PGND.
- 3. Pulse duration  $\leq 100 \ \mu$ s, duty cycle  $\leq 2\%$
- 4. DRAIN supply voltage = 15 V, starting junction temperature, (TJS) = 25°C, L = 100 mH, IAS = 1 A (see Figure 4).

#### DISSIPATION RATING TABLE

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 125°C POWER RATING
DW	1125 mW	9.0 mW/°C	225 mW
Ν	1150 mW	9.2 mW/°C	230 mW



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# recommended operating conditions over recommended operating temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>	4.5	5.5	V
High-level input voltage, VIH	0.85 V <sub>CC</sub>		V
Low-level input voltage, VIL		0.15 V <sub>CC</sub>	V
Pulsed drain output current, $T_C = 25^{\circ}C$ , $V_{CC} = 5 V$ (see Notes 3 and 5)	-1.8	1.5	А
Setup time, D high before $\overline{G}$ , t <sub>SU</sub> (see Figure 2)	10		ns
Hold time, D high after $\overline{G}$ , t <sub>h</sub> (see Figure 2)	5		ns
Pulse duration, t <sub>w</sub> (see Figure 2)	15		ns
Operating case temperature, T <sub>C</sub>	-40	125	°C

### electrical characteristics, $V_{CC}$ = 5 V, $T_C$ = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDITI	ONS	MIN	TYP	MAX	UNIT
V <sub>(BR)</sub> DSX	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA			45			V
V <sub>SD</sub>	Source-drain diode forward voltage	I <sub>F</sub> = 250 mA,	See Note 3			0.85	1	V
Iн	High-level input current	V <sub>CC</sub> = 5.5 V,	$V_I = V_{CC}$				1	μΑ
۱ <sub>IL</sub>	Low-level input current	V <sub>CC</sub> = 5.5 V,	$V_{I} = 0$				-1	μΑ
ICC	Logic supply current	I <sub>O</sub> = 0,	All inputs low			15	100	μΑ
I <sub>N</sub>	Nominal current	V <sub>DS(on)</sub> = 0.5 V See Notes 5, 6,	′,  I <sub>N</sub> = I <sub>D</sub> , and 7	T <sub>C</sub> = 85°C,		250		mA
Inev	Off-state drain current	V <sub>DS</sub> = 40 V				0.05	1	
IDSX	On-state drain current	V <sub>DS</sub> = 40 V,	T <sub>C</sub> = 125°C			0.15	5	μA
		I <sub>D</sub> = 250 mA,	$V_{CC} = 4.5 V$			1.3	2	
<sup>r</sup> DS(on)	Static drain-source on-state resistance	I <sub>D</sub> = 250 mA, V <sub>CC</sub> = 4.5 V	T <sub>C</sub> = 125°C,	See Notes 5 and 6 and Figures 8 and 9		2	3.2	Ω
		I <sub>D</sub> = 500 mA,	V <sub>CC</sub> = 4.5 V			1.3	2	

### switching characteristics, V<sub>CC</sub> = 5 V, T<sub>C</sub> = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<sup>t</sup> PLH	Propagation delay time, low-to-high-level output from D			625		ns
<sup>t</sup> PHL	Propagation delay time, high-to-low-level output from D	C <sub>L</sub> = 30 pF, I <sub>D</sub> = 250 mA,		140		ns
tr	Rise time, drain output	See Figures 1, 2, and $10$		650		ns
t <sub>f</sub>	Fall time, drain output			400		ns
ta	Reverse-recovery-current rise time	I <sub>F</sub> = 250 mA, di/dt = 20 A/µs,		100		
t <sub>rr</sub>	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		ns

NOTES: 3. Pulse duration  $\leq 100 \ \mu$ s, duty cycle  $\leq 2\%$ 

5. Technique should limit  $T_J-T_C$  to 10°C maximum.

6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

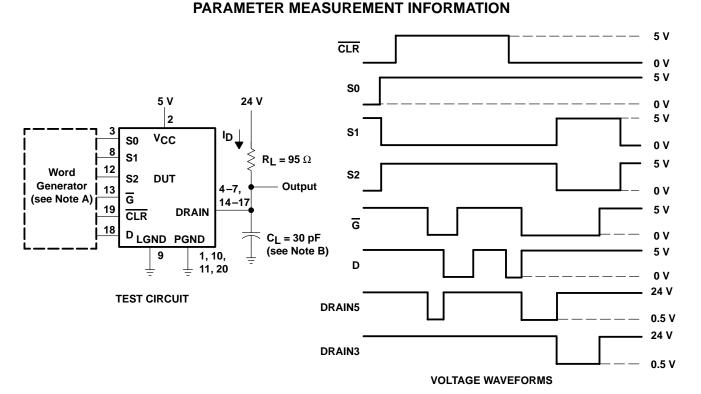
Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T<sub>C</sub> = 85°C.

#### thermal resistance

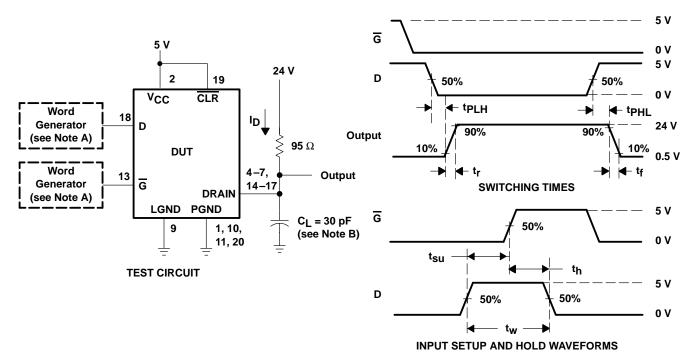
	PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
R <sub>0JA</sub> T	Thermel resistance innetion to embient	DW package	All Q outputs with agual power		111	°C/W
	Thermal resistance junction-to-ambient	N package	All 8 outputs with equal power		108	C/W



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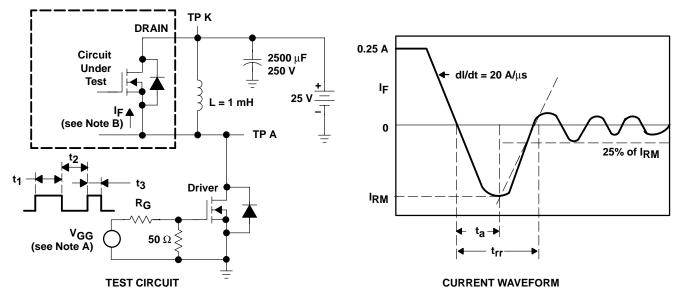




- NOTES: A. The word generator has the following characteristics:  $t_f \le 10$  ns,  $t_f \le 10$  ns,  $t_W = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_O = 50 \ \Omega$ .
  - B. C<sub>L</sub> includes probe and jig capacitance.



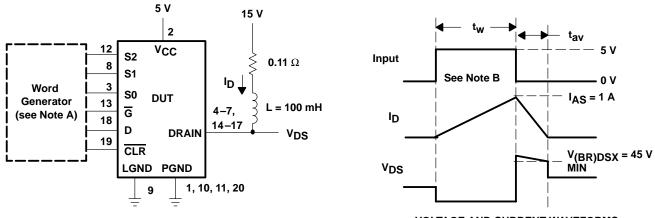
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#### PARAMETER MEASUREMENT INFORMATION

- NOTES: A. The V<sub>GG</sub> amplitude and R<sub>G</sub> are adjusted for di/dt = 20 A/ $\mu$ s. A V<sub>GG</sub> double-pulse train is used to set I<sub>F</sub> = 0.25 A, where t<sub>1</sub> = 10  $\mu$ s, t<sub>2</sub> = 7  $\mu$ s, and t<sub>3</sub> = 3  $\mu$ s.
  - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

#### Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode





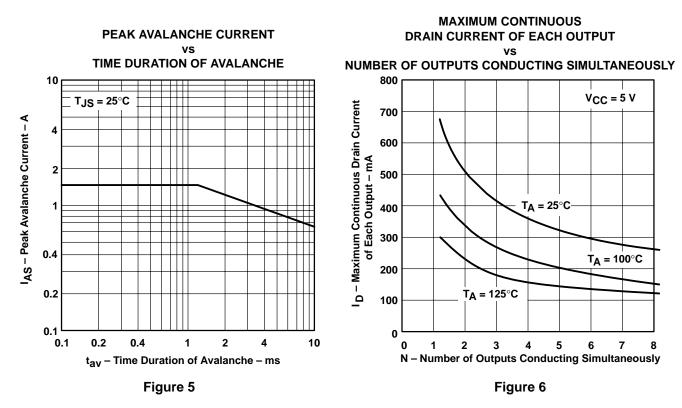


- NOTES: A. The pulse generator has the following characteristics:  $t_f \le 10$  ns,  $t_f \le 10$  ns,  $Z_0 = 50 \Omega$ .
  - B. Input pulse duration, t<sub>W</sub>, is increased until peak current I<sub>AS</sub> = 1 A. Energy test level is defined as  $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{aV}/2 = 75$  mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

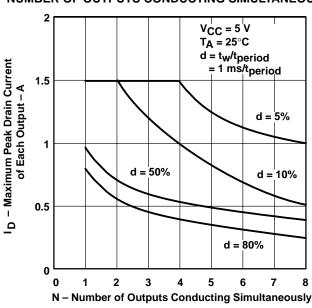


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**TYPICAL CHARACTERISTICS** 

MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT vs

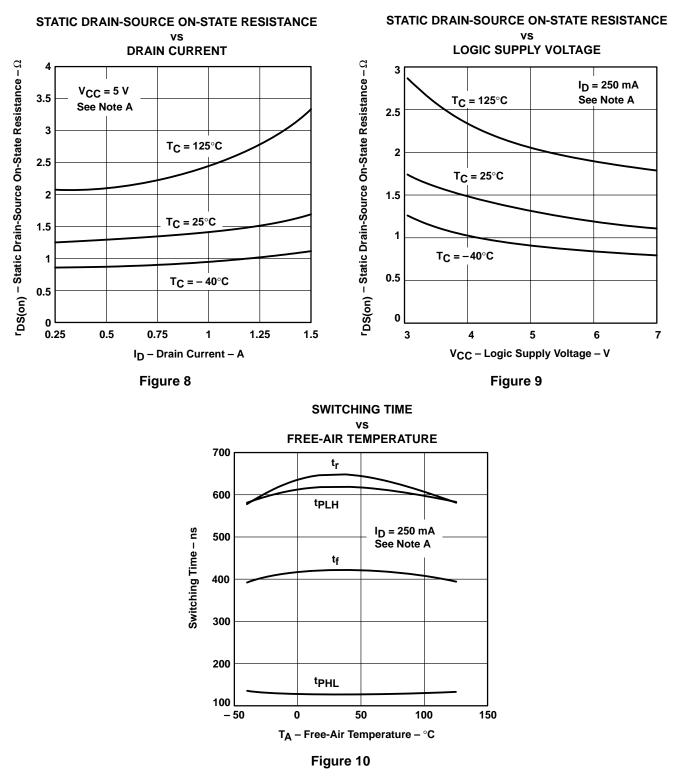


NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

Figure 7



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#### **TYPICAL CHARACTERISTICS**

NOTE A: Technique should limit  $T_J-T_C$  to 10°C maximum.





20-Jan-2016

### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPIC6259DW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259	Samples
TPIC6259DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		TPIC6259	Samples
TPIC6259DWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259	Samples
TPIC6259DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		TPIC6259	Samples
TPIC6259N	ACTIVE	PDIP	Ν	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 125	TPIC6259N	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



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# PACKAGE OPTION ADDENDUM

20-Jan-2016

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION





# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6259DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

TEXAS INSTRUMENTS

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# PACKAGE MATERIALS INFORMATION

4-Jan-2013



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6259DWR	SOIC	DW	20	2000	367.0	367.0	45.0

# N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



# **DW0020A**



# **PACKAGE OUTLINE**

### SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



# DW0020A

# **EXAMPLE BOARD LAYOUT**

### SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DW0020A

# **EXAMPLE STENCIL DESIGN**

### SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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